



America Semiconductor

**Silicon Bridge
Rectifier**

**G2SBA06 thru
G2SBA10**

V_{RRM} = 50 V - 1000 V

I_F = 1.5 A

Features

- Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- Types up to 1000 V V_{RRM}
- Ideal for printed circuit board
- High surge current capability
- High temperature soldering guaranteed: 250°C/ 10 seconds, 0.375(9.5mm) lead length
- Glass passivated chip junction
- High case dielectric strength

GBL Package



Mechanical Data

Case: Molded plastic body over passivated junctions

Weight: 0.071 oz, 2 g

Mounting position: Any

Terminals: Plated leads, solderable per MIL-STD-750

Method 2026 guaranteed

Maximum ratings, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	G2SBA06	G2SBA08	G2SBA10	Unit
Repetitive peak reverse voltage	V _{RRM}		600	800	1000	V
RMS reverse voltage	V _{RMS}		420	560	700	V
DC blocking voltage	V _{DC}		600	800	1000	V
Continuous forward current	I _F	T _C ≤ 25 °C	1.5	1.5	1.5	A
Surge non-repetitive forward current, Half Sine Wave	I _{F,SM}	T _C = 25 °C, t _p = 8.3 ms	60	60	60	A
Operating temperature	T _j		-55 to 150	-55 to 150	-55 to 150	°C
Storage temperature	T _{stg}		-55 to 150	-55 to 150	-55 to 150	°C

Electrical characteristics, at T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	G2SBA06	G2SBA08	G2SBA10	Unit
Diode forward voltage	V _F	I _F = 0.75 A, T _j = 25 °C	1.05	1.05	1.05	V
Reverse current	I _R	V _R = 50 V, T _j = 25 °C	5	5	5	μA
		V _R = 50 V, T _j = 125 °C	500	500	500	

Thermal characteristics

Parameter	Symbol	Conditions	G2SBA06	G2SBA08	G2SBA10	Unit
Thermal resistance, junction - case	R _{thJA}		40.0	40.0	40.0	°C/W
	R _{thJL}		12.0	12.0	12.0	



